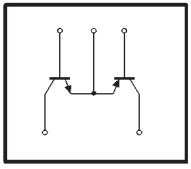
General purpose (dual transistors)

FMY5

●**Features**

1) Both the 2SA1514K and 2SC3906K chips in an SMT package.
2) PNP and NPN chips are connected in a common emitter configuration.

●**Circuit diagram**



●**Absolute maximum ratings** (**Ta=25℃**)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	120	V	
Collector-emitter voltage	V_{CEO}	120	V	
Emitter-base voltage	V_{EBO}	5	V	
Collector current	I_C	50	mA	
Power dissipation	P_C	300 (TOTAL)	mW	*
Junction temperature	Tj	150	℃	
Storage temperature	Tstg	−55～+150	℃	

* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

●**Package, marking, and packaging specifications**

Part No.	FMY5
Package	SMT5
Marking	Y5
Code	T148
Basic ordering unit (pieces)	3000

●**Electrical characteristics** (**Ta=25℃**)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	120	—	—	V	I_C=50/−50 μA
Collector-emitter breakdown voltage	BV_{CEO}	120	—	—	V	I_C=1/−1mA
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	I_E=50/−50 μA
Collector cutoff current	I_{CBO}	—	—	0.5	μA	V_{CB}=100/−100V
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	V_{EB}=4/−4V
DC current transfer ratio	h_{FE}	120	—	820	—	V_{CE}=6/−6V, I_C=2/−2mA
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	I_C=10/−10mA, I_B=1/−0.1mA
Transition frequency	f_T	—	140	—	MHz	V_{CE}=12/−12V, I_E=2/−2mA, f=100MHz *
Output capacitance	Cob	—	3/4	—	pF	V_{CB}=12/−12V, I_E=0A, f=1MHz

Note:The slash denotes NPN/PNP. PNP type negative symbols have been omitted. *Transition frequency of the device.

(94S-440-AC41)

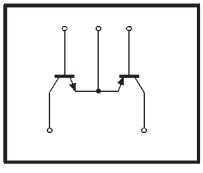
Totempoles (dual transistors)

FMY6

●**Features**

1) Both the 2SA1036K and 2SC2411K chips in an SMT package.
2) PNP and NPN chips are connected in a common emitter configuration.
3) High $I_{Cmax.}$ (Max. 500mA)

●**Circuit diagram**



●**Absolute maximum ratings** (**Ta=25℃**)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	V_{CBO}	40	V	
Collector-emitter voltage	V_{CEO}	32	V	
Emitter-base voltage	V_{EBO}	5	V	
Collector current	I_C	500	mA	
Power dissipation	Pd	300 (TOTAL)	mW	*
Junction temperature	Tj	150	℃	
Storage temperature	Tstg	−55～+150	℃	

* 200mW per element must not be exceeded. PNP type negative symbols have been omitted.

●**Package, marking, and packaging specifications**

Part No.	FMY6
Package	SMT5
Marking	Y6
Code	T148
Basic ordering unit (pieces)	3000

●**Electrical characteristics** (**Ta=25℃**)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	40	—	—	V	I_C=100/−100 μA
Collector-emitter breakdown voltage	BV_{CEO}	32	—	—	V	I_C=1/−1mA
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	I_E=100/−100 μA
Collector cutoff current	I_{CBO}	—	—	1	μA	V_{CB}=20/−20V
Emitter cutoff current	I_{EBO}	—	—	1	μA	V_{EB}=4/−4V
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.4	V	I_C=100/−100mA, I_B=10/−10mA
DC current transfer ratio	h_{FE}	120	—	—	—	V_{CE}/I_C=3/−3V, I_C=10/−10mA
Transition frequency	f_T	—	250/200	—	MHz	V_{CE}=5/−5V, I_E=20/−20mA, f=200MHz *
Output capacitance	Cob	—	6.5/7	—	pF	V_{CE}=10/−10V, I_E=0A, f=1MHz

Note: The slash denotes NPN/PNP. PNP type negative symbols have been omitted. *Transition frequency of mounted transistor.

(96-438-BD11)